L Number	Hits	Search Text	DB	Time stamp
5	32	"sealant material" adj "epoxy"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/02 16:30
6	0	"liquid crystal" adj "sealant material" adj "epoxy"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/02 16:30
7	0	"liquid crystal" adj "sealant material"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/02 16:31
8	3	"liquid crystal" near "sealant material"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/02 16:31
-	2	"6330099"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/02 16:28
-	2	"6362861"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/02 10:29
-	2231	"Agilent Technologies".AS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/02 10:36
-	0	"Agilent Technologies".AS. and 349/190	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/02 10:37
-	0	"anistropic etch" adj "filling hole"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/02 10:46
-	0	"anistropic etch" adj "liquid crystal filling hole"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/02 10:47
-	0	"anistropic etch" adj "liquid crystal"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/02 10:48
-	153	(349/190).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/02 15:20
-	440	(438/30).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/02 12:46
-	1	"anisotropic etch" adj "silicon wafer"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/02 12:55

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-	3	"anisotropic etch" near "silicon wafer"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/02 12:56
-	61	"anisotropic etching" adj "silicon wafer"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/02 13:14
-	0	"anisotropic etching" near "liquid crystal"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/02 13:15
-	0	"anisotropic etching" near "liquid crystal substrate"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/02 13:15
-	708	"anisotropic etching" near "substrate"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/02 13:23
-	144	(349/154).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/02 13:26
-	10	"injection hole" adj "substrate"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/02 13:43
-	0	"sealant" adj "glue, epoxy, solder"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/02 13:46
-	0	"sealant material" adj "glue, epoxy,and solder"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/02 13:46
-	311	"sealant" adj "epoxy"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/02 13:54
-	3	"liquid crystal" adj "microdisplays"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/02 14:22
-	83	"testing" adj "liquid crystal display"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/02 14:29
-	0	"testing" adj "liquid crystal micro display"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/02 14:27
-	0	"testing" adj "sealing hole"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/02 14:29

-	0	"testing" adj " liquid crystal sealing hole"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/02 14:30
-	2	"6330099"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/02 15:09
-	0	(349/190 and testing).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/02 15:18
-	0	349/190 adj testing	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/02 15:18
-	0	349/190 near testing	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/02 15:18
-	0	"349/190" near "testing"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/02 15:18
-	0	"349/190" adj "testing"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/02 15:18
-	475	(438/15).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/02 15:21
-	98	(injection hole) adj (glue)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/02 16:19

438/15 → Key to successful search because Applicant's methods are drawn from semiconductor technology <testing; failure analysis>